

SAM™ Data Sheet SAM-1550-2-2ps-x, λ = 1550 nm

High reflection band $\lambda = 1480 \dots 1580 \text{ nm}$ Absorbance $A_0 = 2 \%$ Modulation depth $\Delta R = 1.2 \%$ Non-saturable loss $A_{ns} = 0.8 \%$ Saturation fluence $\Phi_{sat} = 120 \ \mu J/cm^2$ Relaxation time constant $\tau \sim 2 \ ps$ Damage threshold $\Phi = 2 \ m J/cm^2$ Chip area $4.0 \ mm \ x \ 4.0 \ mm;$ other dimensions on requestChip thickness $450 \ \mu m$ Protectionthe SAM is protected with a dielectric front layerMounting option x denotes the type of mounting as follows: $u mmounted$	Laser wavelength	$\lambda = 1550 \text{ nm}$
Modulation depth $\Delta R = 1.2 \%$ Non-saturable loss $A_{ns} = 0.8 \%$ Saturation fluence $\Phi_{sat} = 120 \ \mu J/cm^2$ Relaxation time constant $\tau \sim 2 \ ps$ Damage threshold $\Phi = 2 \ m J/cm^2$ Chip area $4.0 \ mm \ x \ 4.0 \ mm;$ other dimensions on requestChip thickness $450 \ \mu m$ Protectionthe SAM is protected with a dielectric front layerMounting option \mathbf{x} denotes the type of mounting as follows: $\mathbf{x} = 0$	High reflection band	λ = 1480 1580 nm
Non-saturable loss $A_{ns} = 0.8 \%$ Saturation fluence $\Phi_{sat} = 120 \ \mu J/cm^2$ Relaxation time constant $\tau \sim 2 \ ps$ Damage threshold $\Phi = 2 \ m J/cm^2$ Chip area $4.0 \ mm \ x \ 4.0 \ mm;$ other dimensions on requestChip thickness $450 \ \mu m$ Protectionthe SAM is protected with a dielectric front layerMounting option \mathbf{x} denotes the type of mounting as follows: $\mathbf{x} = 0$	Absorbance	A ₀ = 2 %
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Relaxation time constant $\tau \sim 2 \text{ ps}$ Damage threshold $\Phi = 2 \text{ mJ/cm}^2$ Chip area $4.0 \text{ mm x } 4.0 \text{ mm}$; other dimensions on requestChip thickness 450 µm Protectionthe SAM is protected with a dielectric front layerMounting option x denotes the type of mounting as follows: $x = 0$	Non-saturable loss	A _{ns} = 0.8 %
Damage threshold $\Phi = 2 \text{ mJ/cm}^2$ Chip area $4.0 \text{ mm x } 4.0 \text{ mm; other dimensions on request}$ Chip thickness 450 µm Protectionthe SAM is protected with a dielectric front layerMounting option x denotes the type of mounting as follows: $x = 0$ unmounted	Saturation fluence	Φ_{sat} = 120 µJ/cm ²
Chip area4.0 mm x 4.0 mm; other dimensions on requestChip thickness450 µmProtectionthe SAM is protected with a dielectric front layerMounting option x denotes the type of mounting as follows: unmounted	Relaxation time constant	τ ~ 2 ps
Chip thickness450 μmProtectionthe SAM is protected with a dielectric front layerMounting option x denotes the type of mounting as follows: x = 0unmounted	Damage threshold	$\Phi = 2 \text{ mJ/cm}^2$
Protectionthe SAM is protected with a dielectric front layerMounting option \mathbf{x} denotes the type of mounting as follows: $\mathbf{x} = 0$ $\mathbf{x} = 0$ unmounted	Chip area	4.0 mm x 4.0 mm; other dimensions on request
Mounting option x denotes the type of mounting as follows: $\mathbf{x} = 0$ unmounted	Chip thickness	450 μm
x = 0 unmounted	Protection	the SAM is protected with a dielectric front layer
v = 12.7 a dued on a gold plated Cu cylinder with 12.7 mm (A		

x = 12.7 gglued on a gold plated Cu-cylinder with 12.7 mm \varnothing x = 25.4 gglued on a gold plated Cu-cylinder with 25.4 mm \varnothing x = 12.7 ssoldered on a gold plated Cu-cylinder with 12.7 mm \varnothing x = 25.4 ssoldered on a gold plated Cu-cylinder with 25.4 mm \varnothing x = FCmounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance

